

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

CoolMOS™ CE

500V CoolMOS™ CE Power Transistor
IPX50R3K0CE

Data Sheet

Rev. 2.2
Final

1 Description

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ CE is a price-performance optimized platform enabling to target cost sensitive applications in Consumer and Lighting markets by still meeting highest efficiency standards. The new series provides all benefits of a fast switching Superjunction MOSFET while not sacrificing ease of use and offering the best cost down performance ratio available on the market.

Features

- Extremely low losses due to very low FOM $R_{DS(on)} \cdot Q_g$ and E_{oss}
- Very high commutation ruggedness
- Easy to use/drive
- Pb-free plating, Halogen free mold compound
- Qualified for standard grade applications

Applications

PFC stages, hard switching PWM stages and resonant switching stages for e.g. PC Silverbox, Adapter, LCD & PDP TV and indoor lighting.

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

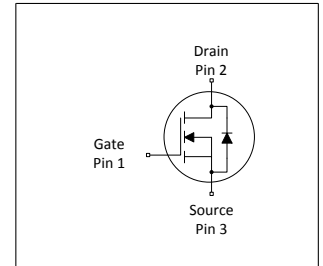
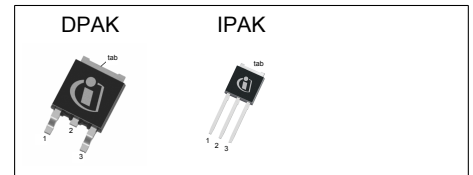


Table 1 Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	550	V
$R_{DS(on),max}$	3	Ω
$Q_{g,typ}$	4.3	nC
$I_{D,pulse}$	4.1	A
$E_{oss}@400V$	0.49	μJ
Body diode di/dt	500	A/ μs

Type / Ordering Code	Package	Marking	Related Links
IPD50R3K0CE	PG-TO 252	50S3K0CE	see Appendix A
IPU50R3K0CE	PG-TO 251		

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2 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	1.7 1.1	A	$T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	4.1	A	$T_C = 25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}	-	-	18	mJ	$I_D = 0.5\text{A}$; $V_{DD} = 50\text{V}$
Avalanche energy, repetitive	E_{AR}	-	-	0.03	mJ	$I_D = 0.5\text{A}$; $V_{DD} = 50\text{V}$
Avalanche current, repetitive	I_{AR}	-	-	0.5	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	50	V/ns	$V_{DS} = 0 \dots 400\text{V}$
Gate source voltage	V_{GS}	-20 -30	-	20 30	V	static; AC ($f > 1\text{ Hz}$)
Power dissipation (non FullPAK) TO-252, TO-251	P_{tot}	-	-	18	W	$T_C = 25^\circ\text{C}$
Operating and storage temperature	T_j, T_{stg}	-55	-	150	$^\circ\text{C}$	-
Continuous diode forward current	I_S	-	-	1.5	A	$T_C = 25^\circ\text{C}$
Diode pulse current ²⁾	$I_{S,pulse}$	-	-	4.1	A	$T_C = 25^\circ\text{C}$
Reverse diode dv/dt ³⁾	dv/dt	-	-	15	V/ns	$V_{DS} = 0 \dots 400\text{V}$, $I_{SD} \leq I_S$, $T_j = 25^\circ\text{C}$, $t_{cond} < 2\mu\text{s}$
Maximum diode commutation speed ³⁾	di/dt	-	-	500	A/ μs	$V_{DS} = 0 \dots 400\text{V}$, $I_{SD} \leq I_S$, $T_j = 25^\circ\text{C}$, $t_{cond} < 2\mu\text{s}$

3 Thermal characteristics

Table 3 Thermal characteristics DPAK, IPAK

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	7.1	$^\circ\text{C/W}$	-
Thermal resistance, junction - ambient ⁴⁾	R_{thJA}	-	- 35	62 -	$^\circ\text{C/W}$	SMD version, device on PCB, minimal footprint SMD version, device on PCB, 6cm ² cooling area ⁴⁾
Soldering temperature, wave- & reflowsoldering allowed	T_{sold}	-	-	260	$^\circ\text{C}$	reflow MSL 1

¹⁾ Limited by $T_{j,max}$. Maximum duty cycle $D = 0.75$

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ $V_{DClink} = 400\text{V}$; $V_{DS,peak} < V_{(BR)DSS}$; identical low side and high side switch with identical R_G

⁴⁾ Device on 40mm*40mm*1.5mm one layer epoxy PCB FR4 with 6cm² copper area (thickness 70 μm) for drain connection. PCB is vertical without air stream cooling.

4 Electrical characteristics

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	500	-	-	V	$V_{GS}=0V, I_D=1mA$
Gate threshold voltage	$V_{(GS)th}$	2.50	3	3.50	V	$V_{DS}=V_{GS}, I_D=0.03mA$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=500V, V_{GS}=0V, T_j=25^\circ C$ $V_{DS}=500V, V_{GS}=0V, T_j=150^\circ C$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	2.70	3.00	Ω	$V_{GS}=13V, I_D=0.4A, T_j=25^\circ C$ $V_{GS}=13V, I_D=0.4A, T_j=150^\circ C$
Gate resistance	R_G	-	6	-	Ω	$f=1\text{ MHz}, \text{open drain}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	84	-	pF	$V_{GS}=0V, V_{DS}=100V, f=1MHz$
Output capacitance	C_{oss}	-	7	-	pF	$V_{GS}=0V, V_{DS}=100V, f=1MHz$
Effective output capacitance, energy related ¹⁾	$C_{o(er)}$	-	6	-	pF	$V_{GS}=0V, V_{DS}=0...400V$
Effective output capacitance, time related ²⁾	$C_{o(tr)}$	-	19	-	pF	$I_D=\text{constant}, V_{GS}=0V, V_{DS}=0...400V$
Turn-on delay time	$t_{d(on)}$	-	7.3	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=0.5A,$ $R_G=5.3\Omega$
Rise time	t_r	-	5.8	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=0.5A,$ $R_G=5.3\Omega$
Turn-off delay time	$t_{d(off)}$	-	23	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=0.5A,$ $R_G=5.3\Omega$
Fall time	t_f	-	49	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=0.5A,$ $R_G=5.3\Omega$

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	0.5	-	nC	$V_{DD}=400V, I_D=0.5A, V_{GS}=0\text{ to }10V$
Gate to drain charge	Q_{gd}	-	2.6	-	nC	$V_{DD}=400V, I_D=0.5A, V_{GS}=0\text{ to }10V$
Gate charge total	Q_g	-	4.3	-	nC	$V_{DD}=400V, I_D=0.5A, V_{GS}=0\text{ to }10V$
Gate plateau voltage	$V_{plateau}$	-	5.3	-	V	$V_{DD}=400V, I_D=0.5A, V_{GS}=0\text{ to }10V$

¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$
²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$

Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.83	-	V	$V_{GS}=0V, I_F=0.5A, T_i=25^\circ C$
Reverse recovery time	t_{rr}	-	99	-	ns	$V_R=400V, I_F=0.5A, di_F/dt=100A/\mu s$
Reverse recovery charge	Q_{rr}	-	0.3	-	μC	$V_R=400V, I_F=0.5A, di_F/dt=100A/\mu s$
Peak reverse recovery current	I_{rrm}	-	4.2	-	A	$V_R=400V, I_F=0.5A, di_F/dt=100A/\mu s$

5 Electrical characteristics diagrams

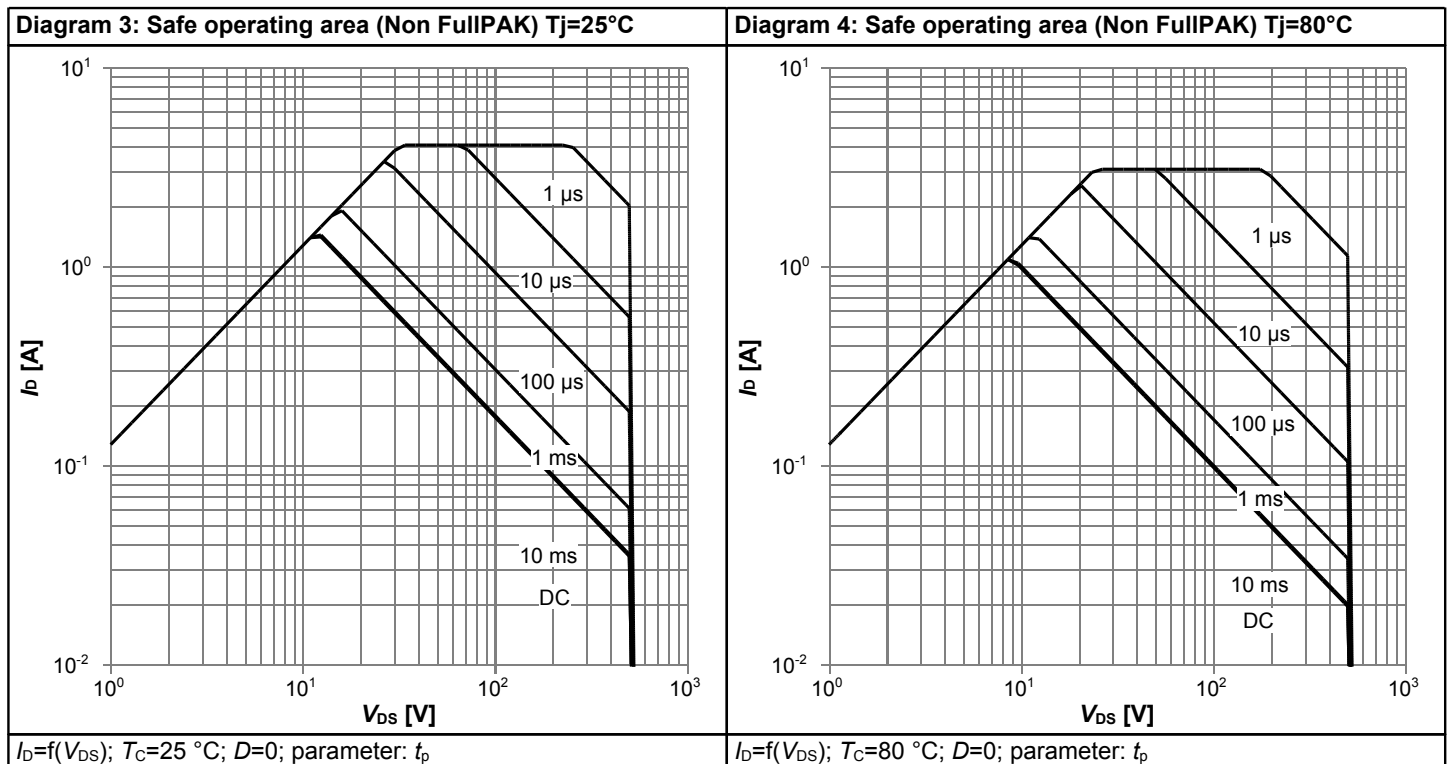
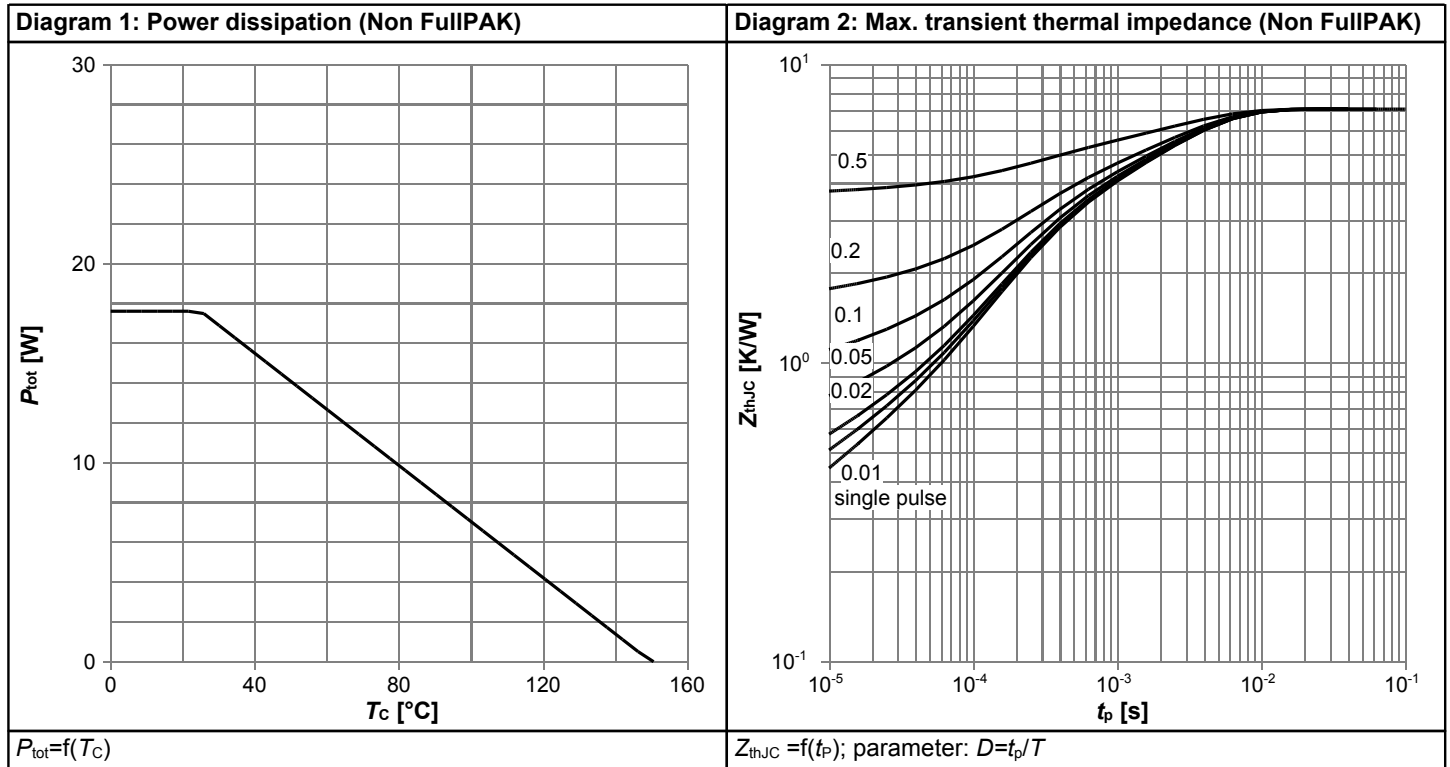
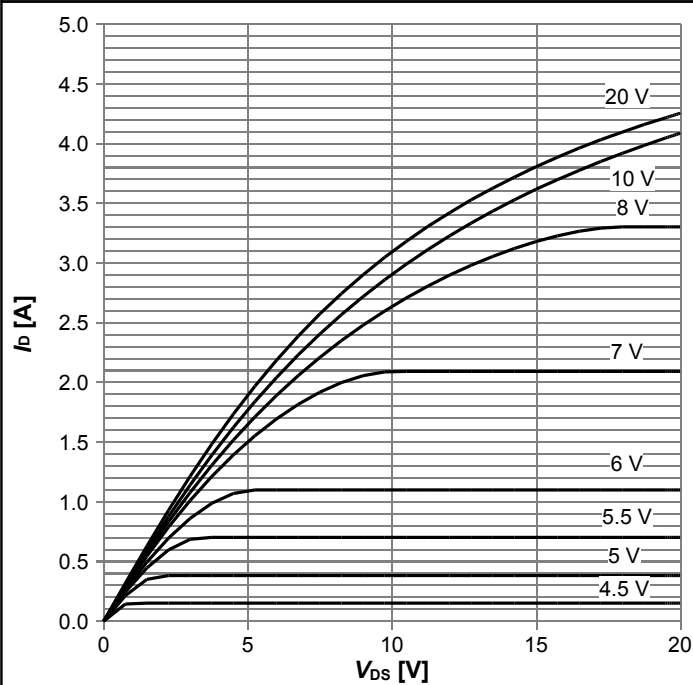
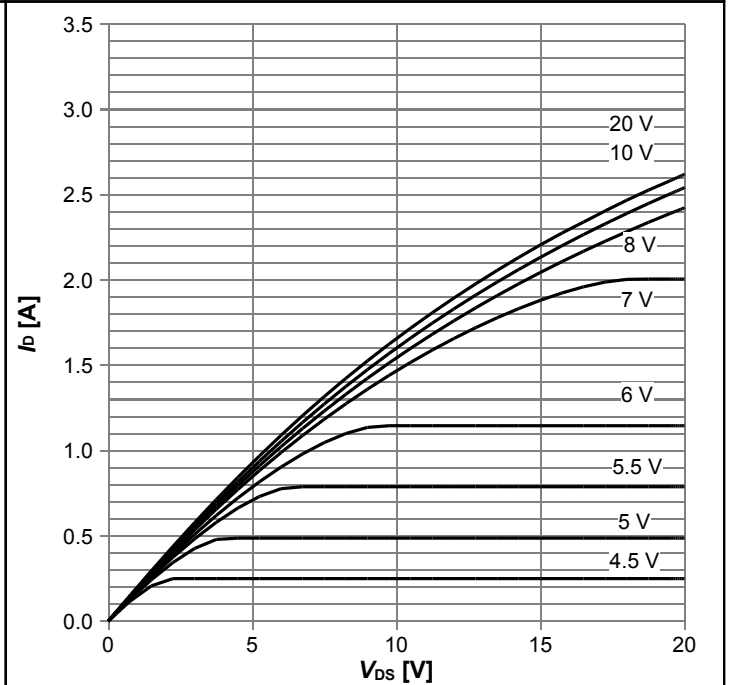


Diagram 5: Typ. output characteristics $T_j=25^\circ\text{C}$



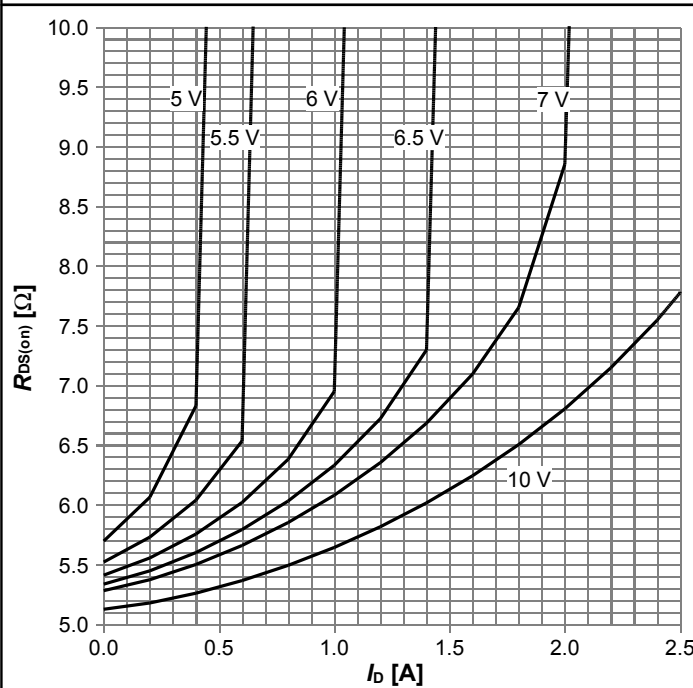
$I_D=f(V_{DS})$; $T_j=25^\circ\text{C}$; parameter: V_{GS}

Diagram 6: Typ. output characteristics $T_j=125^\circ\text{C}$



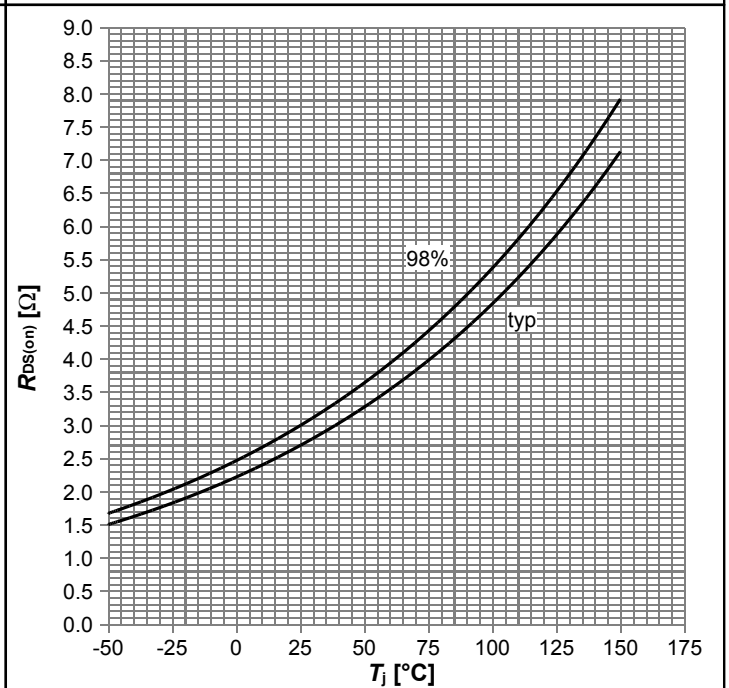
$I_D=f(V_{DS})$; $T_j=125^\circ\text{C}$; parameter: V_{GS}

Diagram 7: Typ. drain-source on-state resistance



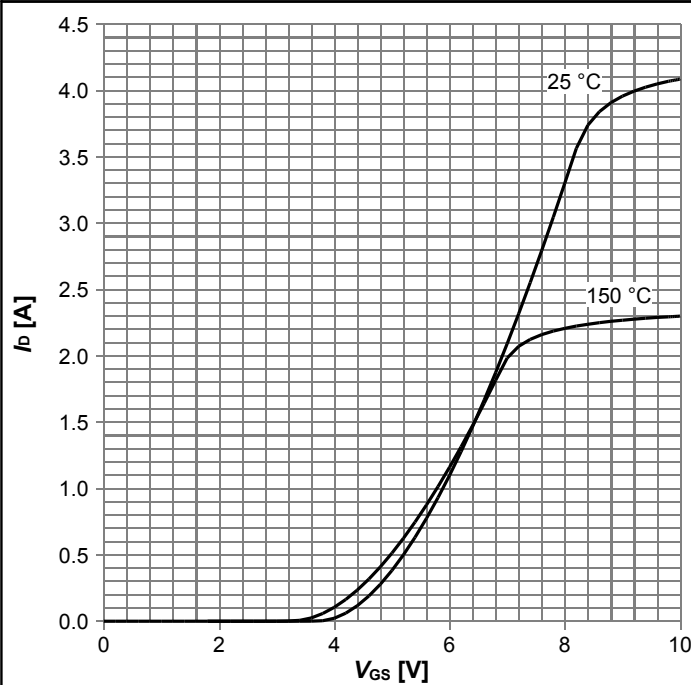
$R_{DS(on)}=f(I_D)$; $T_j=125^\circ\text{C}$; parameter: V_{GS}

Diagram 8: Drain-source on-state resistance



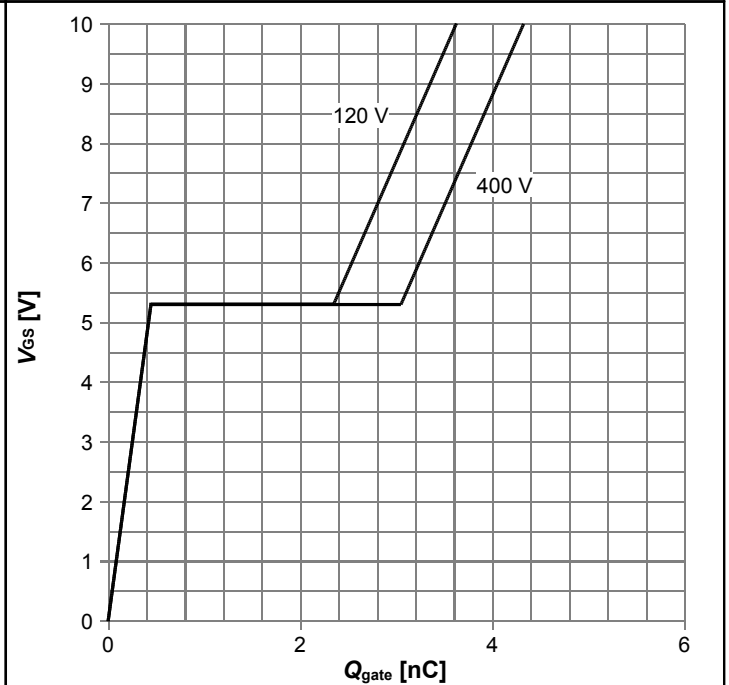
$R_{DS(on)}=f(T_j)$; $I_D=0.4\text{ A}$; $V_{GS}=13\text{ V}$

Diagram 9: Typ. transfer characteristics



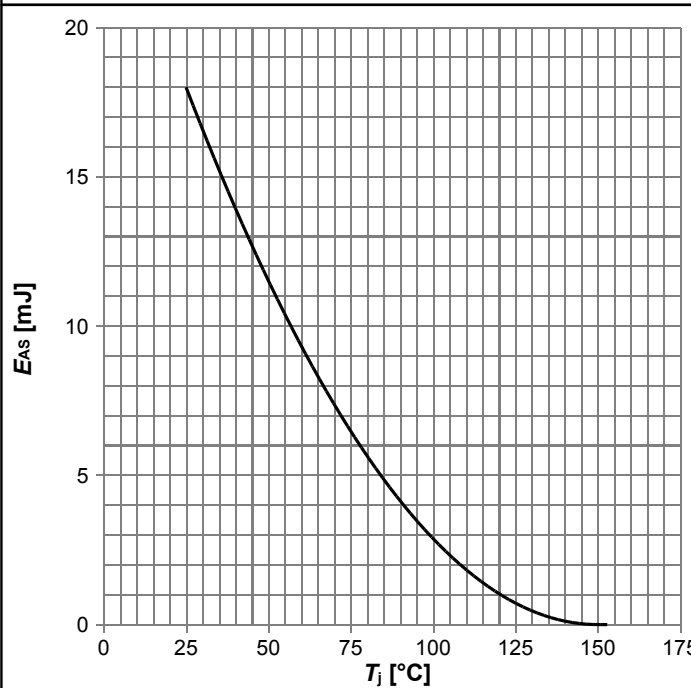
$I_D=f(V_{GS}); V_{DS}=20V$; parameter: T_j

Diagram 10: Typ. gate charge



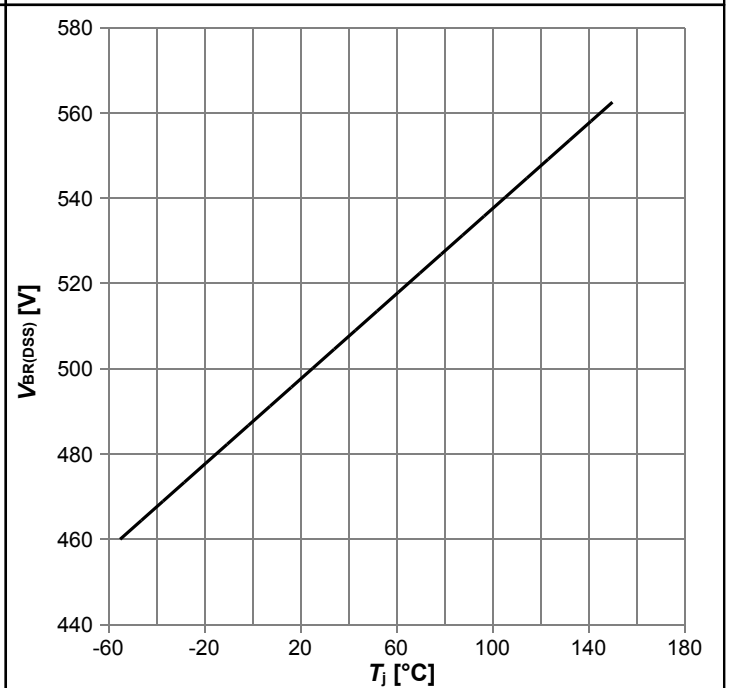
$V_{GS}=f(Q_{gate}); I_D=0.5\text{ A pulsed}$; parameter: V_{DD}

Diagram 11: Avalanche energy



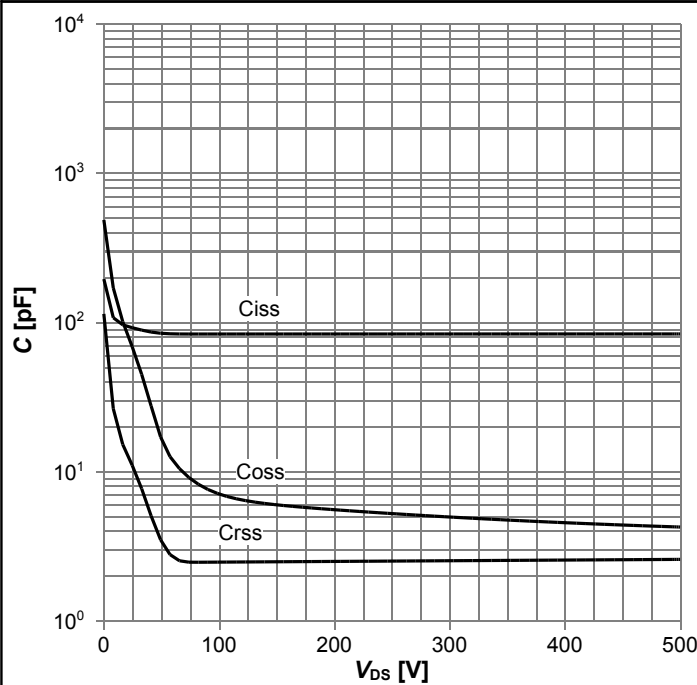
$E_{AS}=f(T_j); I_D=0.5\text{ A}; V_{DD}=50\text{ V}$

Diagram 12: Drain-source breakdown voltage



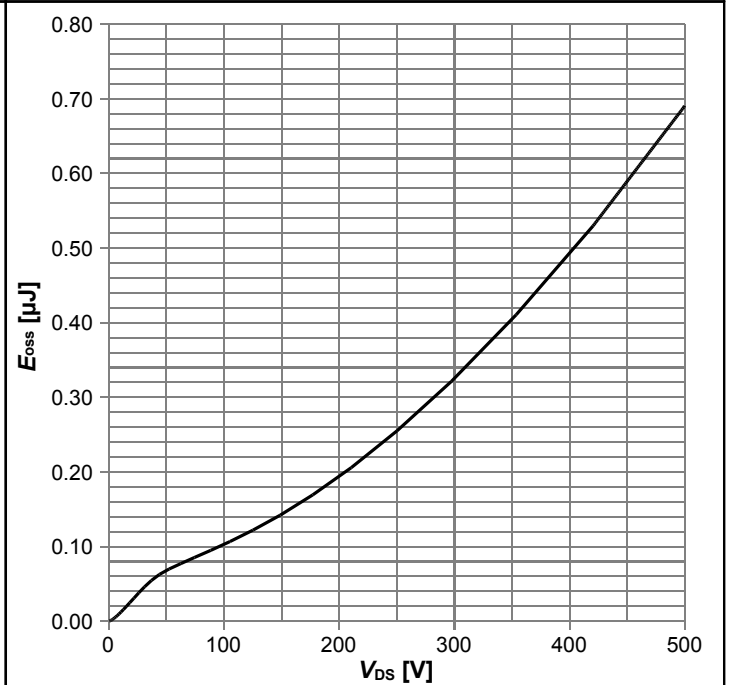
$V_{BR(DSS)}=f(T_j); I_D=1\text{ mA}$

Diagram 13: Typ. capacitances



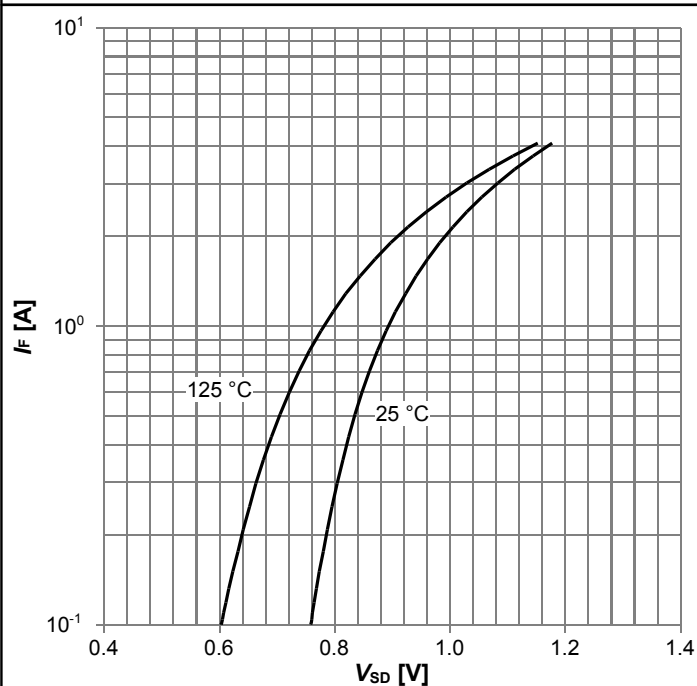
$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$

Diagram 14: Typ. Coss stored energy



$E_{oss}=f(V_{DS})$

Diagram 15: Forward characteristics of reverse diode



$I_F=f(V_{SD}); \text{parameter: } T_j$

6 Test Circuits

Table 8 Diode characteristics

Test circuit for diode characteristics	Diode recovery waveform
<p>$R_{g1} = R_{g2}$</p>	<p>$t_{rr} = t_F + t_S$ $Q_r = Q_F + Q_S$</p>

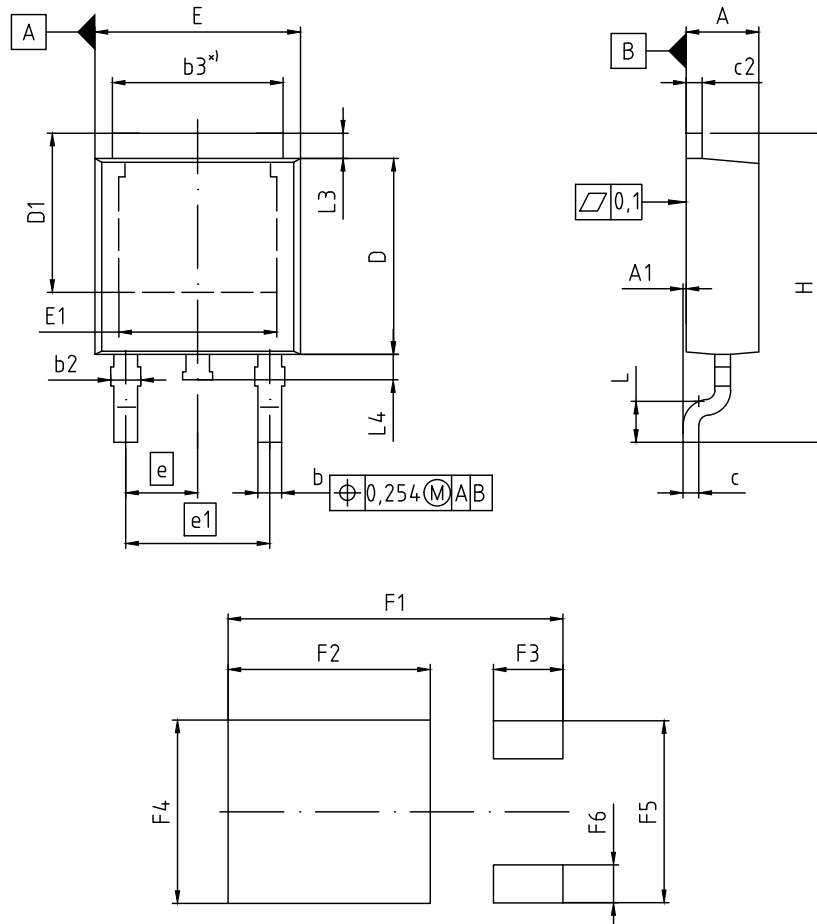
Table 9 Switching times

Switching times test circuit for inductive load	Switching times waveform

Table 10 Unclamped inductive load

Unclamped inductive load test circuit	Unclamped inductive waveform

7 Package Outlines



*) mold flash not included

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.00	0.15	0.000	0.006
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b3	5.00	5.50	0.197	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.98	0.018	0.039
D	5.97	6.22	0.235	0.245
D1	5.02	5.84	0.198	0.230
E	6.40	6.73	0.252	0.265
E1	4.70	5.60	0.185	0.220
e	2.29 (BSC)		0.090 (BSC)	
e1	4.57 (BSC)		0.180 (BSC)	
N	3		3	
H	9.40	10.48	0.370	0.413
L	1.18	1.70	0.046	0.067
L3	0.90	1.25	0.035	0.049
L4	0.51	1.00	0.020	0.039
F1	10.60		0.417	
F2	6.40		0.252	
F3	2.20		0.087	
F4	5.80		0.228	
F5	5.76		0.227	
F6	1.20		0.047	

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Figure 1 Outline PG-TO 252, dimensions in mm/inches

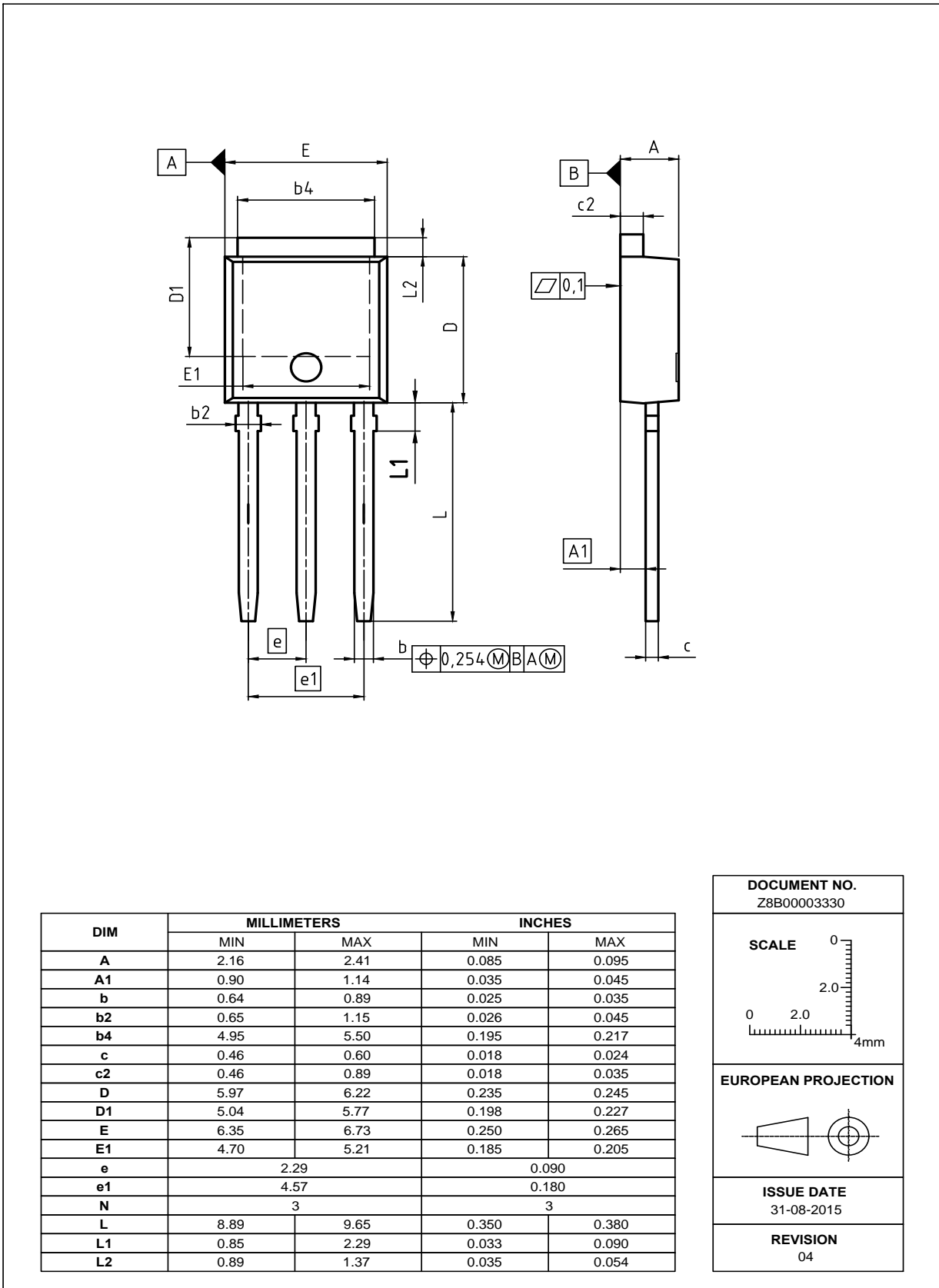


Figure 2 Outline PG-TO 251, dimensions in mm/inches

8 Appendix A

Table 11 Related Links

- IFX CoolMOS Webpage: www.infineon.com
- IFX Design tools: www.infineon.com

Revision History

IPD50R3K0CE, IPU50R3K0CE

Revision: 2015-11-17, Rev. 2.2

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2012-12-05	Release of final version
2.1	2013-07-16	update to Halogen free mold compound
2.2	2015-11-17	Updated to qualified for standard grade & updated package drawing

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